

1.Description

This P-Channel enhancement mode field effect transistors is produced using Fairchild's proprietary, high cell density, DMOSTechnology. This very high density process is tailored to minimize on-state resistance at low gate drive conditions.

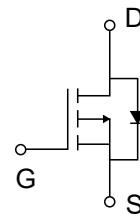
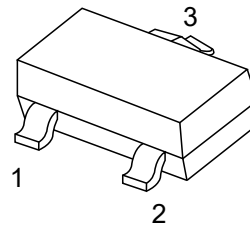
2.Features

- $V_{DS(V)} = -30V$
- $I_D = -4.2A (V_{GS} = -10V)$
- $R_{DS(ON)} < 65m\Omega (V_{GS} = -4.5V)$
- $R_{DS(ON)} < 120m\Omega (V_{GS} = -2.5V)$

3.Pinning information

Pin	Symbol	Description
1	G	GATE
2	S	SOURCE
3	D	DRAIN

SOT-23



4.Absolute Maximum Ratings $T_A = 25^\circ C$

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltage		V _{GS}	±12	
Continuous Drain Current	T _A =25°C	I _D	-4.2	A
	T _A =70°C		-3.5	
Pulsed Drain Current		I _{DM}	-30	
Power Dissipation	T _A =25°C	P _D	1.4	W
	T _A =70°C		1	
Thermal Resistance.Junction- to-Ambient t ≤ 10s		R _{thJA}	90	°C/W
Thermal Resistance.Junction- to-Ambient			125	
Thermal Resistance.Junction- to-Case		R _{thJC}	60	
Junction Temperature		T _J	150	°C
Junction and Storage Temperature Range		T _{STG}	-55 to 150	



5. Electrical Characteristics $T_A = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24\text{V}$, $V_{GS} = 0\text{V}$			-1	μA
		$V_{DS} = -24\text{V}$, $V_{GS} = 0\text{V}$, $T_J = 55^\circ\text{C}$			-5	
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 12\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\mu\text{A}$	-0.4		-1.3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5\text{V}$, $I_D = -4\text{A}$			65	m Ω
		$V_{GS} = -2.5\text{V}$, $I_D = -1\text{A}$			120	
On state drain current	$I_{D(on)}$	$V_{GS} = -4.5\text{V}$, $V_{DS} = -5\text{V}$	-25			A
Forward Transconductance	g_{FS}	$V_{DS} = -5\text{V}$, $I_D = -5\text{A}$	7	11		S
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = -15\text{V}$, $f = 1\text{MHz}$		954		pF
Output Capacitance	C_{oss}			115		
Reverse Transfer Capacitance	C_{rss}			77		
Gate resistance	R_g	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$, $f = 1\text{MHz}$		6		Ω
Total Gate Charge	Q_g	$V_{GS} = -4.5\text{V}$, $V_{DS} = -15\text{V}$ $I_D = -4\text{A}$		9.4		nC
Gate Source Charge	Q_{gs}			2		
Gate Drain Charge	Q_{gd}			3		
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = -10\text{V}$, $V_{DS} = -15\text{V}$ $R_L = 3.6\Omega$, $R_{GEN} = 6\Omega$		6.3		ns
Turn-On Rise Time	t_r			3.2		
Turn-Off DelayTime	$t_{D(off)}$			38.3		
Turn-Off Fall Time	t_f			12		
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -4\text{A}$, $dI/dt = 100\text{A}/\mu\text{s}$		20.2		
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = -5\text{A}$, $dI/dt = 100\text{A}/\mu\text{s}$		11.2		nC
Maximum Body-Diode Continuous Current	I_S				-2.2	A
Diode Forward Voltage	V_{SD}	$I_S = -1\text{A}$, $V_{GS} = 0\text{V}$		-0.75	-1	V



6.1 Typical Characteristics

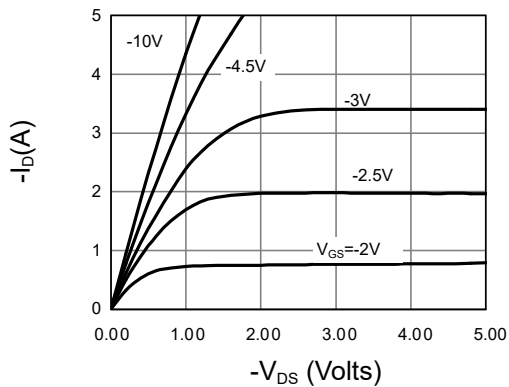


Fig 1: On-Region Characteristics

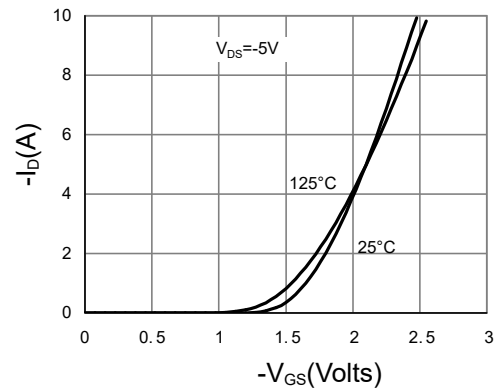


Figure 2: Transfer Characteristics

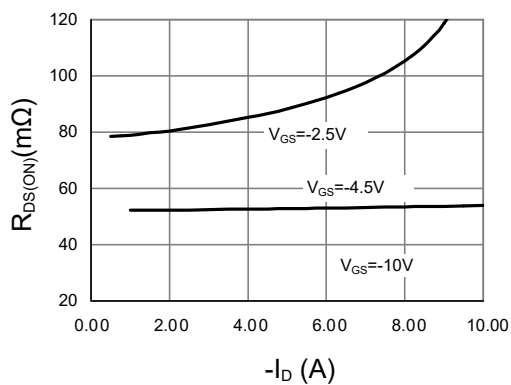


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

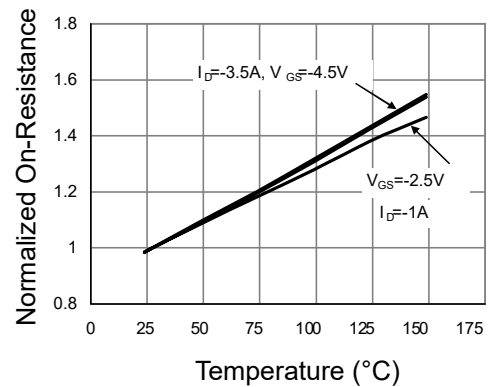


Figure 4: On-Resistance vs. Junction Temperature

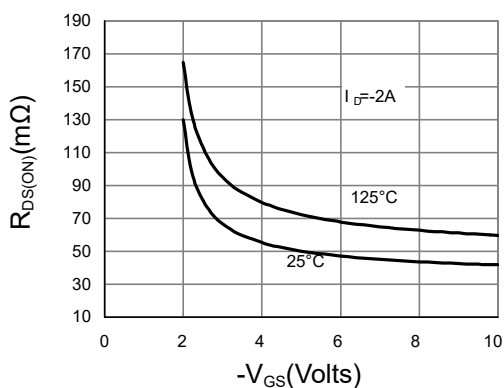


Figure 5: On-Resistance vs. Gate-Source Voltage

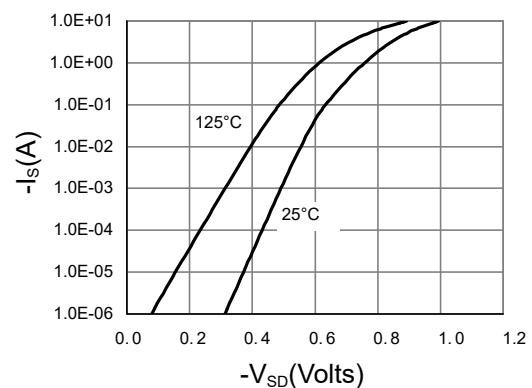


Figure 6: Body-Diode Characteristics



6.2 Typical Characteristics

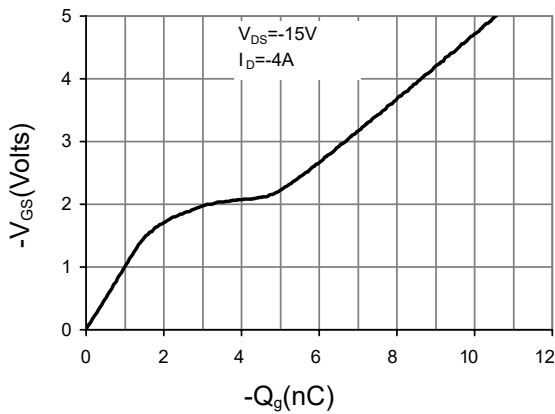


Figure 7: Gate-Charge Characteristics

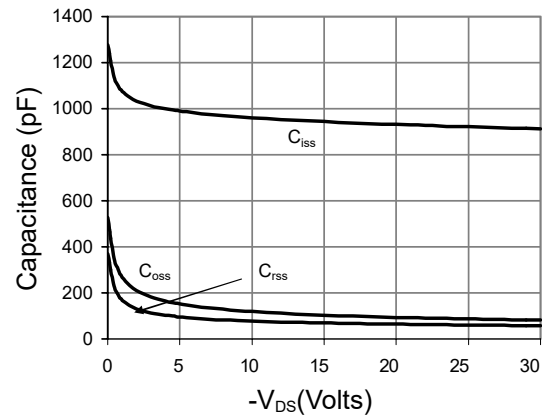


Figure 8: Capacitance Characteristics

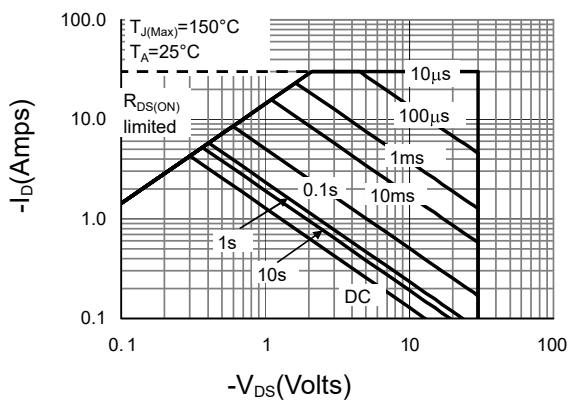


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

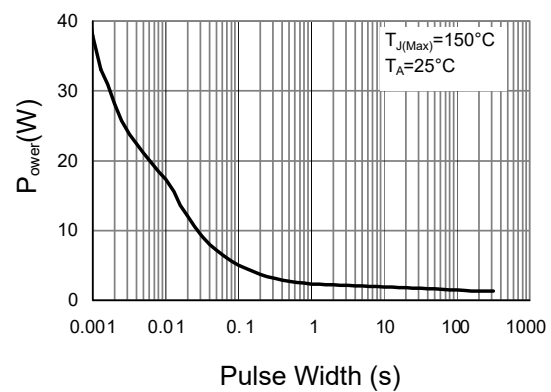


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

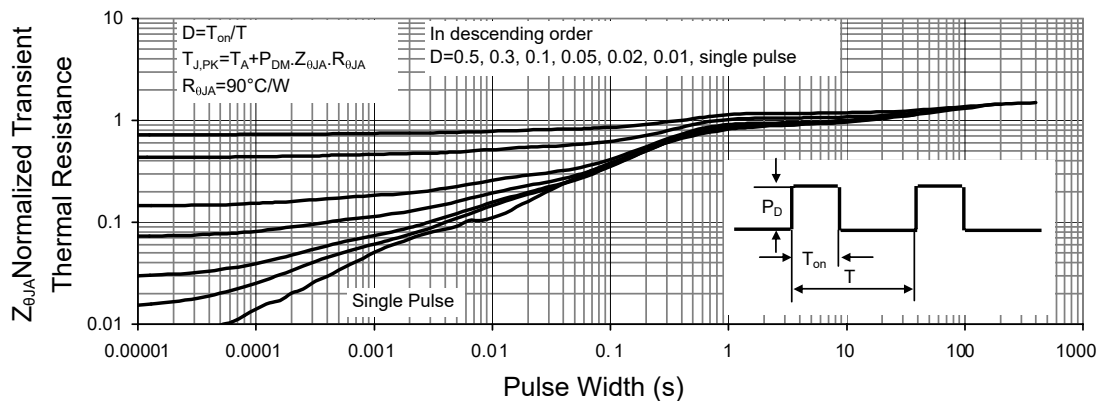
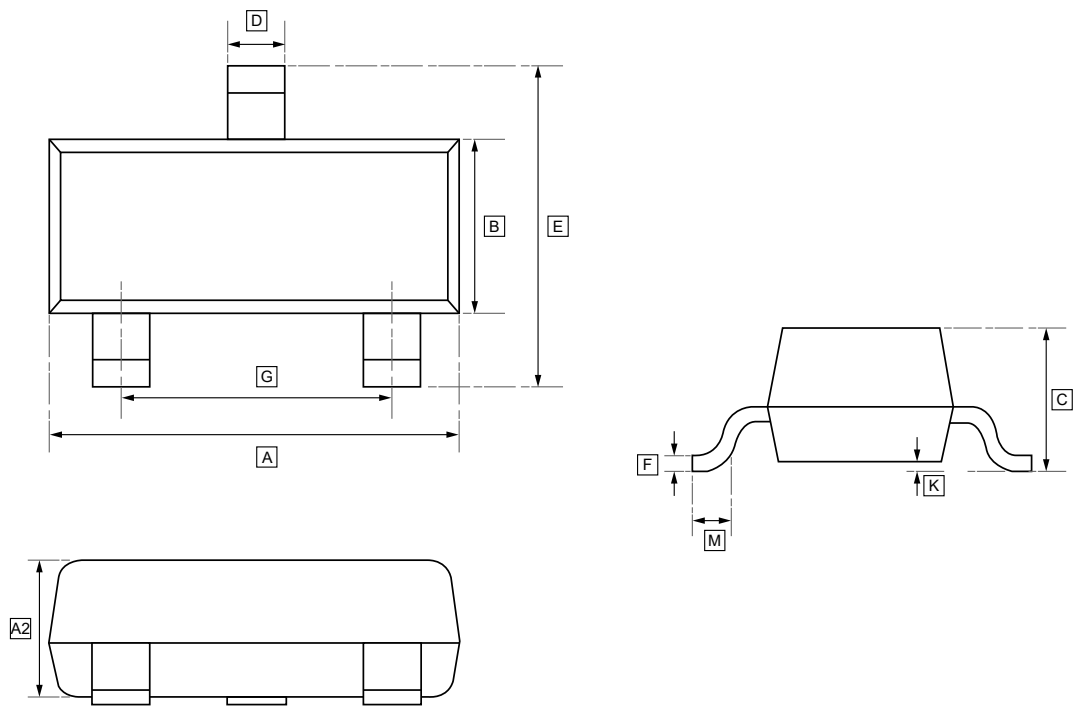


Figure 11: Normalized Maximum Transient Thermal Impedance



7.SOT-23 Package Outline Dimensions

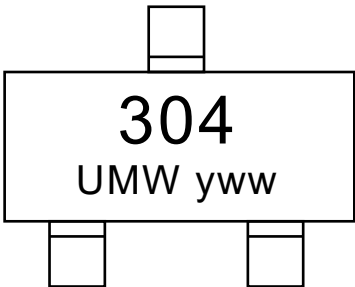


DIMENSIONS (mm are the original dimensions)

Symbol	A	B	C	D	E	G	K	M	A2	F
Min	2.85	1.20	0.90	0.40	2.25	1.80	0.00	0.30	0.95	0.095
Max	3.04	1.40	1.10	0.50	2.55	2.00	0.10	-	1.05	0.115



8.Ordering Information



yww: Batch Code

Order Code	Package	Base QTY	Delivery Mode
UMW FDV304P	SOT-23	3000	Tape and reel



9.Disclaimer

UMW reserves the right to make changes to all products, specifications. Customers should obtain the latest version of product documentation and verify the completeness and currency of the information before placing an order.

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